



# Schottky Barrier Diode

## Features

1. High reliability
2. Low reverse current and low forward voltage



## Applications

Low current rectification and high speed switching

## Construction

Silicon epitaxial planar

## Absolute Maximum Ratings

$T_j=25\text{ }^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		LL60	$V_{RRM}$	40	V
		LL60P	$V_{RRM}$	45	V
Peak forward surge current	$t_p \leq 1\text{ s}$	LL60	$I_{FSM}$	150	mA
		LL60P	$I_{FSM}$	500	mA
Forward continuous current	$T_a=25\text{ }^{\circ}\text{C}$	LL60	$I_F$	30	mA
		LL60P	$I_F$	50	mA
Storage temperature range			$T_{stg}$	-65~+125	$^{\circ}\text{C}$

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

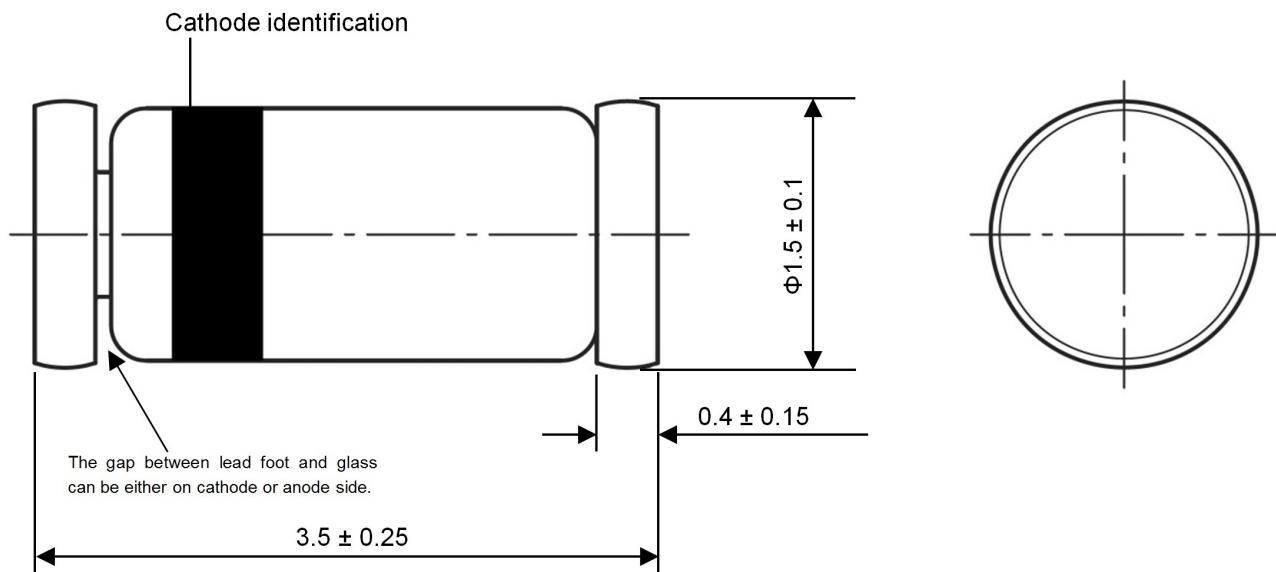


**Electrical Characteristics**

$T_j=25\text{ }^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	LL60	$V_F$		0.32	0.5	V
		LL60P	$V_F$		0.24	0.5	V
	$I_F=30\text{mA}$	LL60	$V_F$		0.65	1.0	V
	$I_F=200\text{mA}$	LL60P	$V_F$		0.65	1.0	V
Reverse current	$V_R=15\text{V}$	LL60	$I_R$		0.1	0.5	$\mu\text{A}$
		LL60P	$I_R$		0.5	1.0	$\mu\text{A}$
Junction capacitance	$V_R=1\text{V}, f=1\text{MHz}$	LL60	$C_J$		2.0		pF
	$V_R=10\text{V}, f=1\text{MHz}$	LL60P	$C_J$		6.0		pF
Reverse recovery time	$I_F=I_R=1\text{mA } I_{tr}=1\text{mA } R_C=100\Omega$		$t_{rr}$			1.0	ns

**Dimensions in mm**



Glass Case  
 Mini Melf / SOD-80  
 JEDEC DO-213 AA